



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: INOUE, et al.

Group Art Unit: 2814

Serial No.: 09/473,988

Examiner: DOAN, Theresa T.

Filed: December 29, 1999

P.T.O. Confirmation No.: 1714

For. SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME

PRELIMINARY AMENDMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Date: July 8, 2003

Sir:

Prior to continued examination, please amend the above-captioned patent application as follows:

IN THE CLAIMS:

Please amend claims 1 and 8 as follows:

1. (Five Times Amended) A semiconductor device comprising an insulating interlayer formed on a conductive film, said insulating interlayer including:
 - a first insulating layer of a composition containing SiH;
 - a second insulating layer formed on said first insulating layer; and
 - a third insulating layer formed between said conductive film and said first insulating layer, wherein said first insulating layer has an H content of not less than 15.4 atom% in the

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